



YEA SHIN TECHNOLOGY CO., LTD

YS4903ZBB

## P-Channel Enhancement MOSFET

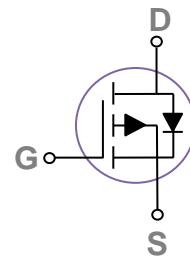
V<sub>D</sub>S= -40V, ID= -38A



### Features

- -30V,-38A, R<sub>D(S)</sub>(ON) = 14mΩ@V<sub>G</sub>S = -10V
- Fast switching
- Green Device Available
- Suit for -4.5V Gate Drive Applications

### PPAK3x3 Pin Configuration



### Applications

- MB / VGA / Vcore
- POL Applications
- Load Switch
- LED Application

### Absolute Maximum Rating T<sub>c</sub>=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>D</sub> S	Drain-Source Voltage	-40	V
V <sub>G</sub> S	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current – Continuous (T <sub>c</sub> =25°C)	-38	A
	Drain Current – Continuous (T <sub>c</sub> =100°C)	-24	A
I <sub>DM</sub>	Drain Current – Pulsed <sup>1</sup>	168	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	61	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	35	A
P <sub>D</sub>	Power Dissipation (T <sub>c</sub> =25°C)	52	W
	Power Dissipation – Derate above 25°C	0.42	W/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction to ambient	---	62	°C /W
R <sub>θJC</sub>	Thermal Resistance Junction to Case	---	2.4	°C /W

# DEVICE CHARACTERISTICS

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Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

### Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=-250\mu\text{A}$	-40	---	---	V
$\text{I}_{\text{DSS}}$	Drain-Source Leakage Current	$\text{V}_{\text{DS}}=-40\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{T}_J=25^\circ\text{C}$	---	---	-1	$\mu\text{A}$
		$\text{V}_{\text{DS}}=-32\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{T}_J=125^\circ\text{C}$	---	---	-10	$\mu\text{A}$
$\text{I}_{\text{GSS}}$	Gate-Source Leakage Current	$\text{V}_{\text{GS}}=\pm 20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA

### On Characteristics

$\text{R}_{\text{DS(ON)}}$	Static Drain-source On-Resistance	$\text{V}_{\text{GS}}=-10\text{V}, \text{I}_D=-15\text{A}$	---	11.3	14	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_D=-8\text{A}$	---	15.6	21	$\text{m}\Omega$
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{GS}}=\text{V}_{\text{DS}}, \text{I}_D=250\mu\text{A}$	-1.0	-1.6	-2.5	V
$\text{g}_{\text{fs}}$	Forward Transconductance	$\text{V}_{\text{DS}}=-10\text{V}, \text{I}_D=-4\text{A}$	---	11	---	S

### Dynamic and Switching Characteristics

$\text{Q}_g$	Total Gate Charge <sup>3,4</sup>	$\text{V}_{\text{DS}}=-32\text{V}, \text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_D=-10\text{A}$	---	22.2	40	nC
$\text{Q}_{\text{gs}}$	Gate-Source Charge <sup>3,4</sup>		---	8.2	16	
$\text{Q}_{\text{gd}}$	Gate-Drain Charge <sup>3,4</sup>		---	8.8	16	
$\text{T}_{\text{d(on)}}$	Turn-On Delay Time <sup>3,4</sup>	$\text{V}_{\text{DD}}=-20\text{V}, \text{V}_{\text{GS}}=-10\text{V}, \text{R}_G=6\Omega, \text{I}_D=-1\text{A}$	---	23	40	ns
$\text{T}_r$	Rise Time <sup>3,4</sup>		---	10	20	
$\text{T}_{\text{d(off)}}$	Turn-On Delay Time <sup>3,4</sup>		---	135	250	
$\text{T}_f$	Fall Time <sup>3,4</sup>		---	46	90	
$\text{C}_{\text{iss}}$	Input Capacitance	$\text{V}_{\text{DS}}=-25\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{f}=1\text{MHz}$	---	2757	4000	pF
$\text{C}_{\text{oss}}$	Output Capacitance		---	240	360	
$\text{C}_{\text{rss}}$	Reverse Transfer Capacitance		---	137	200	

### Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$\text{I}_s$	Continuous Source Current	$\text{V}_G=\text{V}_D=0\text{V}$ , Force Current	---	---	-38	A
$\text{I}_{\text{SM}}$	Pulsed Source Current		---	---	-76	A
$\text{V}_{\text{SD}}$	Diode Forward Voltage	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_s=-1\text{A}, \text{T}_J=25^\circ\text{C}$	---	---	-1	V

Note :

- Repetitive Rating : Pulsed width limited by maximum junction temperature.
- $\text{V}_{\text{DD}}=25\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{L}=0.1\text{mH}, \text{I}_{\text{AS}}=51\text{A}, \text{R}_G=25\Omega$ , Starting  $\text{T}_J=25^\circ\text{C}$ .
- The data tested by pulsed , pulse width  $\leq 300\text{us}$  , duty cycle  $\leq 2\%$ .
- Essentially independent of operating temperature.

# DEVICE CHARACTERISTICS

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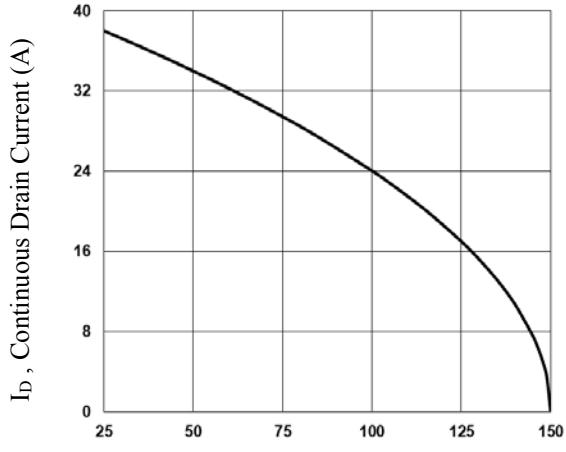


Fig.1      Continuous Drain Current vs.  $T_c$

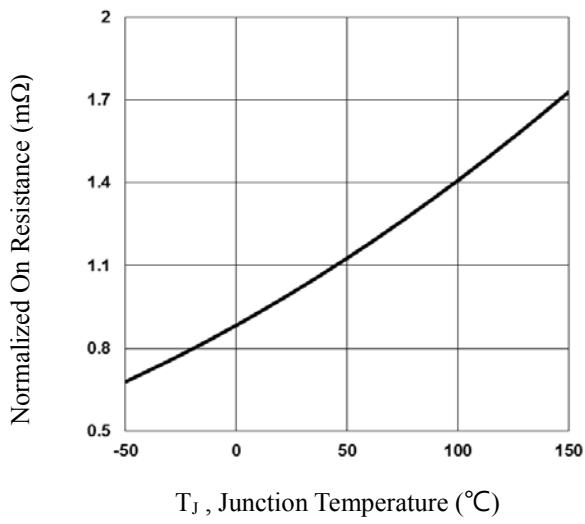


Fig.2      Normalized RDSON vs.  $T_j$

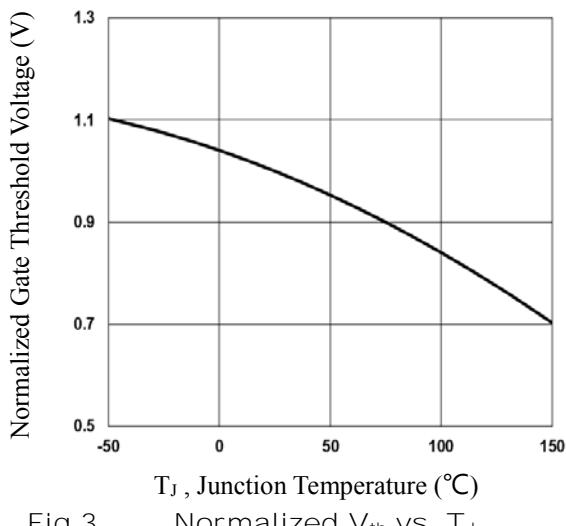


Fig.3      Normalized  $V_{th}$  vs.  $T_j$

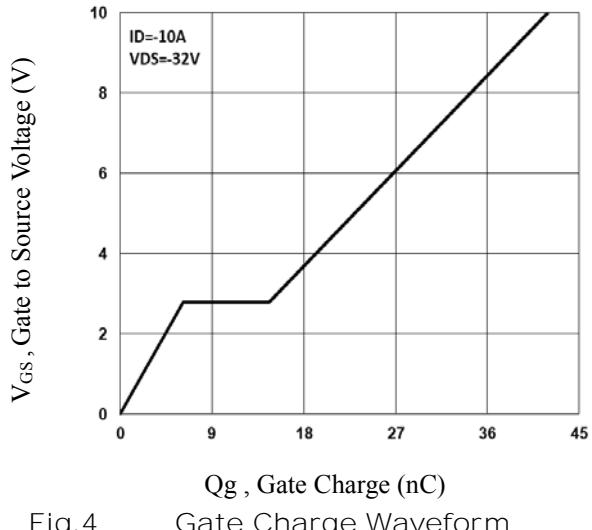


Fig.4      Gate Charge Waveform

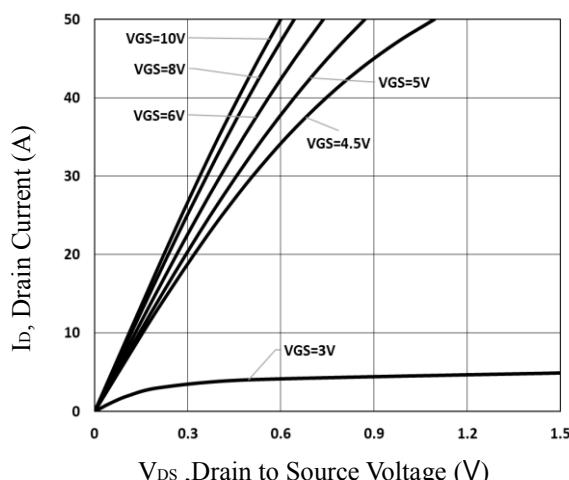


Fig.5      Typical Output Characteristics

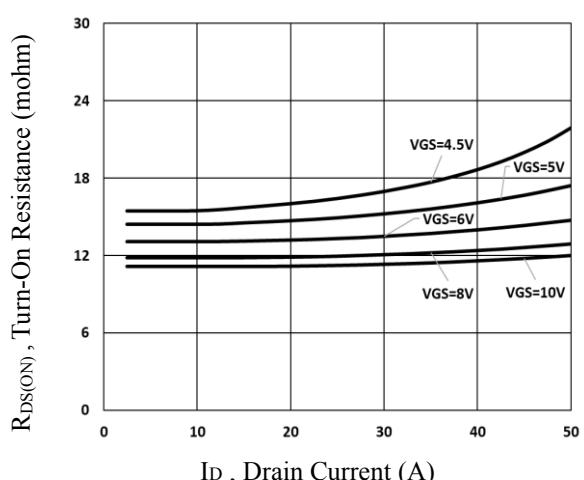


Fig.6      Turn-On Resistance vs.  $I_D$

# DEVICE CHARACTERISTICS

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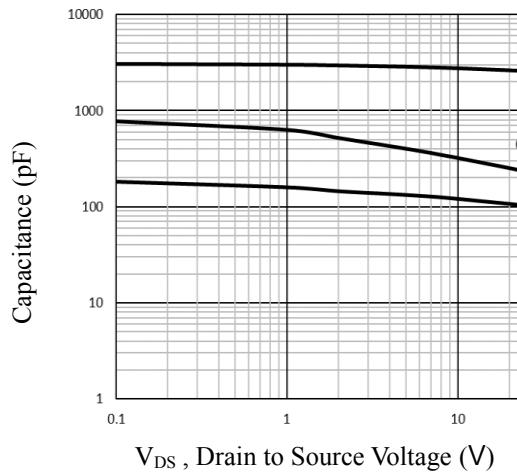


Fig.7 Capacitance Characteristics

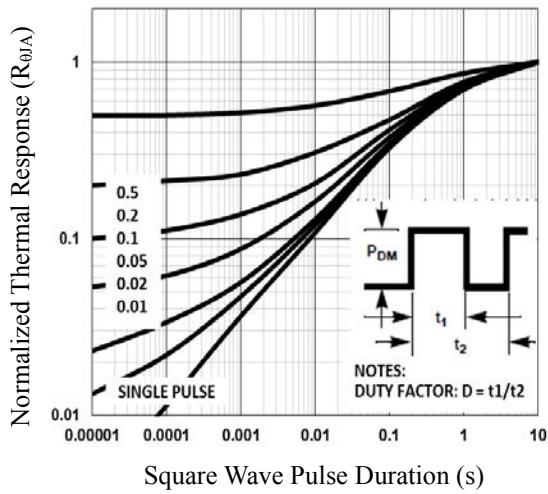


Fig.8 Normalized Transient Impedance

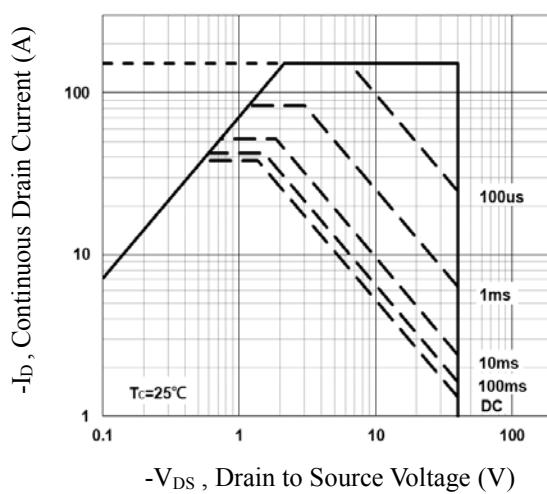


Fig.9 Maximum Safe Operation Area

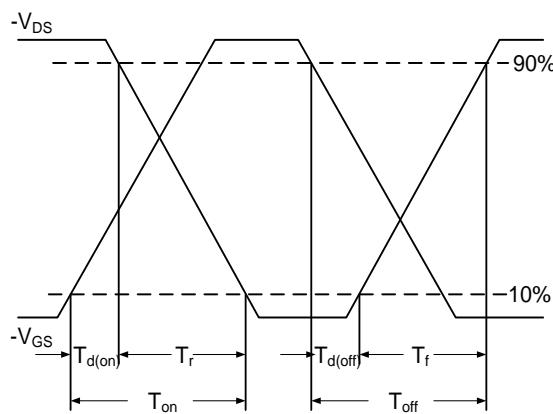


Fig.10 Switching Time Waveform

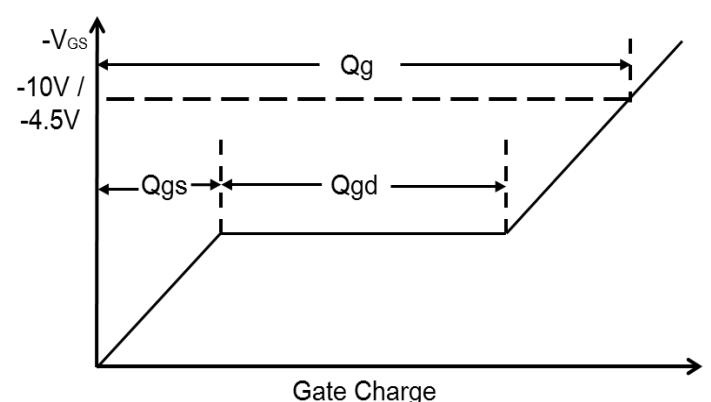
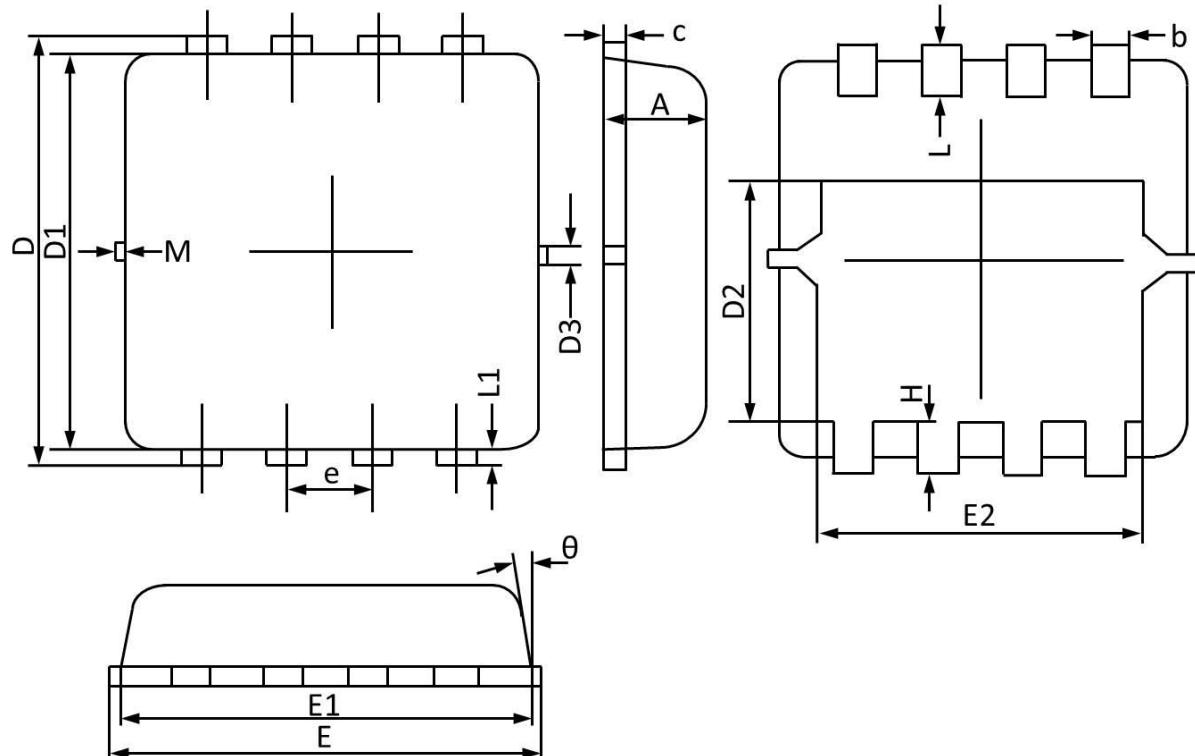


Fig.11 Gate Charge Waveform

# PACKAGE OUTLINE & DIMENSIONS

YS4903ZBB

## PPAK3x3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
b	0.250	0.350	0.010	0.013
c	0.100	0.250	0.004	0.009
D	3.250	3.450	0.128	0.135
D1	3.000	3.200	0.119	0.125
D2	1.780	1.980	0.070	0.077
D3	0.130 REF		0.005 REF	
E	3.200	3.400	0.126	0.133
E1	3.000	3.200	0.119	0.125
E2	2.390	2.590	0.094	0.102
e	0.650 BSC		0.026 BSC	
H	0.300	0.500	0.011	0.019
L	0.300	0.500	0.011	0.019
L1	0.130 REF		0.005 REF	
θ	0°	12°	0°	12°
M	0.150 REF		0.006 REF	